### In the claims:

1. (previously presented) A method and system of wire bonding a semiconductor die to a lead, comprising the steps of:

attaching a first end of a first bonding wire to a semiconductor die with a ball bond;

attaching a second end of the first bonding wire to an interposer pad with a stitch bond;

attaching a first end of a second bonding wire to the interposer pad with a ball bond; and

attaching the second end of the second bonding wire to the lead with a stitch bond.

2. (previously presented) The method and system of wire bonding a semiconductor die to a lead as recited in Claim 1, wherein the first bonding wire and second bonding wire are made of a gold-based material.

# 3-4. (canceled)

5. (previously presented) The method and system of wire bonding a semiconductor die to a lead as recited in Claim1, wherein the interposer pad has x-y dimensions of between approximately 58 micrometers to 88 micrometers along an x-axis and 88 micrometers along a y-axis.

6. (previously presented) The method and system of wire bonding a semiconductor die to a lead as recited in Claim1, for use in ball bond grid array packages.

### 7. (canceled)

- 8. (previously presented) A semiconductor device comprisisng:
- a semiconductor die disposed on a substrate;
- a plurality of interposer pads on said substrate;
- a plurality of leads on the substrate;
- a plurality of bonding wires attached to the semiconductor die with ball bonds and to the leads with stitch bonds, said wires attached to said interposer pads.
- 9. (previously presented) The semiconductor device as recited in Claim 8, wherein the plurality of bonding wires are comprised of gold-based material.

# 10. (canceled)

11. (previously presented) The semiconductor device as recited in Claim 8, wherein each of said bonding wires comprises a bonding wire between the semiconductor die and each interposer pad attached to a bonding pad on the semiconductor die with a ball bond and to said interposer pad with a stitch bond and a bonding wire between the interposer pad and the lead attached to the interposer pad with a ball bond and to each lead with a stitch bond.

- 12. (previously presented) The semiconductor device as recited in Claim 8, wherein the interposer pads are dimensioned from 58 micrometers to 88 micrometers along an x-axis and from 88 to 125 micrometers along a y-axis.
- 13. (previously presented) The semiconductor device as recited in Claim 8, wherein the semiconductor package comprises a ball grid array.

#### 14. (canceled)

- 15. (previously presented) The semiconductor device as recited in Claim 8 wherein an interposer pad electrically floats on the substrate.
- 16. (previously presented) A method of fabricating a semiconductor device, comprising:

attaching a sem iconductor die to a substrate having a plurality of leads and a plurality of interposer pads arranged around said die;

coupling the die to the plurality of interposer pads with a first plurality of bonding wires ball bonded to said die and stitch bonded tosaid interposer pads; and

coupling the plurality of interposer pads to the plurality of leads with a second plurality of bonding wires ball bonded to said interposer pads and stitch bonded to said leads.

17. (previously presented) The method of fabricating a semiconductor device as recited i Claim 16, wherein the plurality of interposer pads electrically float on the semiconductor package.

- 18. (previously presented) The method of fabricating a semiconductor device as recited i Claim 16, wherein the plurality of interposer pads electrically float on the semiconducor package.
- 19. (canceled) The method of fabricating a semiconductor device as recited i Claim 16, wherein the semiconductor package interposer pads are fabricated on an elector-less substrate.
- 20. (previously presented) The method of fabricating a semiconductor device as recited i Claim 16, wherein the placement of the interposer pads are are operable to reduce wire sweep.
- 21. (previously presented) The method of fabricating a semiconductor device as recited i Claim 16, wherein the semiconductor package comprises a ball grid array.

22. (canceled)